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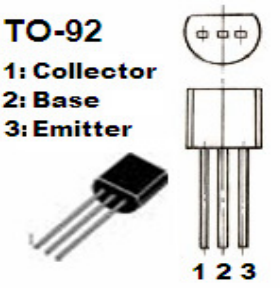
PNP Transistor
BC556/557/558

Features:

- High Current transistor



Maximum Rating (TA=25℃ unless otherwise note)

Parameter		Symbol	Value	Units
Collector-Base Voltage	BC556	V_{CBO}	-80	V
	BC557		-50	
	BC558		-30	
Collector-Emitter Voltage		V_{CEO}	-65 -45 -30	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current –Continuous		IC	-100	mA
Collector Power Dissipation		PC	625	mW
Junction Temperature		TJ	150	℃
Storage Temperature		Tstg	-55-150	℃

Electrical Characteristics (Tamb=25℃unless otherwise specified):

Parameter	Symbol	Test conditions		MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	I_C=-100uA, I_E=0	**BC556**	-80			V
			BC557	-50			
			BC558	-30			
Collector-emitter breakdown voltage	V_{CEO}	I_C=-2mA, I_B=0	**BC556**	-65			V
			BC557	-45			
			BC558	-30			
Emitter-base breakdown voltage	V_{CBO}	I_E=-100uA, I_C=0		-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -70 V,I_E=0	**BC556**			-0.1	uA
		V_{CB}= -45 V,I_E=0	**BC557**				
		V_{CB}= -25 V,I_E=0	**BC558**				
Collector cut-off current	I_{EBO}	V_{CE}= -60 V,I_B=0	**BC556**			-0.1	μA
		V_{CE}= -40 V,I_B=0	**BC557**				
		V_{CE}= -25 V, I_B=0	**BC558**				
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0	**BC556**			-0.1	μA
			BC557				
			BC558				
DC current gain	h_{FE}	V_{CE}=-5V, I_C= -2mA	**BC556**	120		800	
			BC557	120		800	
			BC558	120		800	
			BC557A	120		220	
			BC556B/BC557B/BC558B	180		460	
			BC557C	420		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-5mA				-0.65	V
Base-emitter voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-5mA				-1	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA,f= 100 MHz			150		MHz